

WHAT IS CLAIMED IS:SUB A147
1.

A method of fabricating a semiconductor device, the method comprising:
depositing a layer to a predetermined thickness on a wafer;
planarizing the deposited layer to remove a portion of the deposited layer, the resulting planarized layer comprising a uniform region of uniform thickness extending along a wafer surface and nearly to an edge of the wafer, and a non-uniform region of non-uniform thickness corresponding to the edge of the wafer;

coating a photoresist layer on the planarized layer;

removing a portion of the coated photoresist layer corresponding to an edge region of the wafer, thereby exposing at least the non-uniform region of the planarized layer;

etching at least the exposed non-uniform region of the planarized layer; and

stripping a remaining portion of the coated photoresist layer on the planarized layer, thereby forming a pattern layer comprising a portion of the uniform region of the planarized layer.

2. The method of claim 1, wherein the planarizing comprises a chemical mechanical polishing (CMP) process.

3. The method of claim 1, wherein the coating of the photoresist layer continues until the photoresist layer has a thickness of approximately 5000-15000 Å.

4. The method of claim 1, wherein the etching comprises a wet etching process.

5. The method of claim 4, wherein the exposing also exposes a portion of the uniform region of the planarized layer.

6. The method of claim 5, wherein the wet etching also removes the exposed portion of the uniform region of the planarized layer.

7. A method of fabricating a semiconductor device, the method comprising:

depositing a layer to a predetermined thickness on a wafer, the deposited

layer comprising a uniform region of uniform thickness extending along a wafer

surface and nearly to an edge of the wafer, and a non-uniform region of non-uniform

thickness corresponding to the edge of the wafer;

coating a photoresist layer on the deposited layer;

removing a portion of the coated photoresist layer corresponding to an edge region of the wafer, thereby exposing at least the non-uniform region of the deposited layer;

etching at least the exposed non-uniform region of the deposited layer;
stripping a remaining portion of the coated photoresist layer on the deposited layer; and
planarizing the uniform region of the deposited layer to thereby forming a pattern layer comprising the uniform region of the planarized layer.

8. The method of claim 7, wherein the planarizing comprises a chemical mechanical polishing (CMP) process.

9. The method of claim 7, wherein the coating of the photoresist layer continues until the photoresist layer has a thickness of approximately 5000-15000 Å.

10. The method of claim 7, wherein the etching comprises a wet etching process.

11. The method of claim 10, wherein the exposing also exposes a portion of the uniform region of the deposited layer.

12. The method of claim 11, wherein the wet etching also removes the exposed portion of the uniform region of the deposited layer.